

IN THE SPECIFICATION:

Please replace the paragraph which begins at the bottom of page 18 and ends at the top of page 19 with the following:

With reference to FIG. 8, as another alternative, capillary columns 214 that include hemispherical grain silicon 216 on the surfaces 215 thereof may be formed in selected regions of a substrate 212 by known techniques. First, an elongate trench 213, which defines the path of the capillary column, is defined in a substrate by known patterning processes, such as mask and etch techniques. The area of the surfaces of trench 213 may then be increased by known methods, such as by forming hemispherical grain silicon 215 thereon. Exemplary methods of forming hemispherical grain silicon that may be employed to fabricate capillary columns 214 include those disclosed in United States Patent ~~5,407,435~~5,407,534, which issued to Randhir P.S. Thakur on April 18, 1995; United States Patent 5,623,243, which issued to Hirohito Watanabe et al. on April 22, 1997; United States Patent 5,634,974, which issued to Ronald A. Weimer et al. on June 3, 1997; United States Patent 5,721,171, which issued to Er-Xuan Ping et al. on February 24, 1998; and United States Patent 5,726,085, which issued to Darius Lammont Crenshaw et al. on March 10, 1998, the disclosures of each of which are hereby incorporated by reference in their entirety. In general, a film of amorphous silicon is formed in trench 213. Impurities are then seeded into the amorphous silicon. Then, the material is annealed to cause nucleation sites to grow at the seeding sites, to thereby form the rough textured hemispherical grain silicon 216. A solid phase 218, such as a native oxide layer, may then be grown on the surface of the hemispherical grain silicon 216. Finally, the entire structure 210 may be enclosed by a cover layer 220 or a suitable package.